Part Number Customer						
Category	Parameter		Specification	Measurement Method		
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm			
	2.0	Primary Flat Orientation	{110}+/-1.0 degree	Wafer Vendor		
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor		
	4.0	Secondary Flat Orientation	none / semi std			
	5.0	Overall Thickness	342.00 +/- 7.00 μm	ADE, 100%		
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process		
	7.0	Bow	<40.00µm	ADE to ASTM F534, 100%		
	8.0	Warp	<40.00µm	ADE to ASTM F657, 100%		
	9.0	Edge Chips	0	Bright Light, 100%		
	10.0	Edge Exclusion	5mm			
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor		
	12.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor		
	13.0	Handle Thickness	300.00 +/- 5.00 μm	ADE, 100%		
	14.0	Handle Doping Type	Р	Wafer Vendor		
	15.0	Handle Dopant	Boron	Wafer Vendor		
	16.0	Handle Resistivity	0.01~0.1 Ohm-cm	Wafer Vendor		
	17.0	Backside Finish	Polished with oxide and lasermark	Wafer Vendor		
BuriedOxide	18.0	Oxide Type	Thermal			
	19.0	Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%		
	20.0	Oxide formed on	Handle Only			
DeviceSilicon	21.0	Device Growth Method	CZ	Wafer Vendor		
	22.0	Device Orientation	{100} +/- 1.0 degree	Wafer Vendor		
	23.0	Nominal Thickness	40.00 +/- 1.00 μm	ADE Single point, 100%		
	24.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process		
	25.0	Device Doping Type	Р	Wafer Vendor		
	26.0	Device Dopant	Boron	Wafer Vendor		
	27.0	Device Resistivity	<0.0015 Ohmcm	Wafer Vendor		
	28.0	Voids	None >3.0mm	SAM, 100% (note 2)		
	29.0	Scratches	0	Bright Light, 100% (note 2)		
	30.0	Haze	none	Bright Light, 100% (note 2)		

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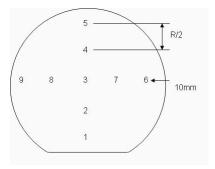
**Product Specification** 

1000.690303

Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	Wafer per box :	Max 25		
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.			

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information